## 2004 Paper 9 Question 2

## VLSI Design

- (a) Sketch designs for an n-input NAND gate in CMOS using
  - (i) static CMOS;
  - (ii) dynamic CMOS;
  - (iii) pseudo-nMOS.

[2 marks each]

(b) Assuming that a conducting p-channel has a resistance  $\gamma$  times that of a similarly sized n-channel, annotate each of your circuit diagrams with suitable widths for the transistors, and explain the reasons for their values.

[2 marks each]

- (c) For each design, calculate the logical effort and the parasitic delay.

  [2 marks each]
- (d) Which is likely to be fastest for the case when n=4 and  $\gamma=3$ ? What difference would it make if the circuit were driving a large capacitative load? [2 marks]